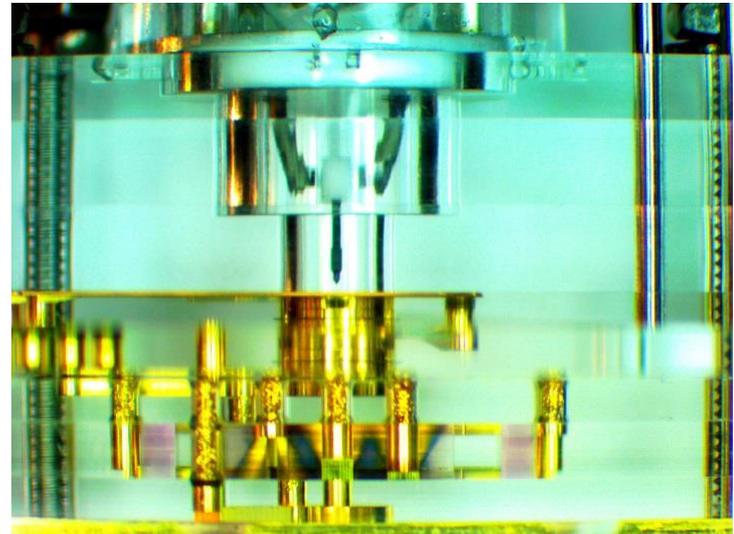
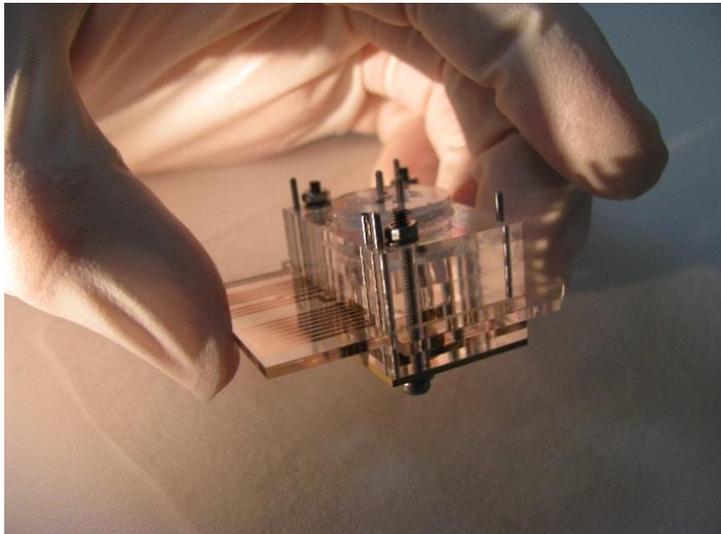


Micro Penning Traps for Continuous Magnetic Field Monitoring in High Radiation Environments

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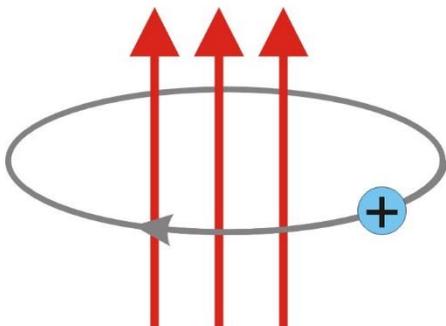
- Need for radiation-resistant magnetic field probes
- Measuring magnetic field with Penning trap
- The MSU minitrap design
- Three-dimensional precision machining of ion microtraps made out of fused silica glass
- The microtrap magnetometer

Need for radiation-resistant, continuous monitoring magnetometer

- Next generation rare isotope beam facilities and accelerators will operate at increased radiation levels.
- Existing semiconductor based probes, nmr probes, have limited lifetime at current radiation levels of operational facilities.
- Magnetic field probes needed at multiple locations in the beam line with different measurement precision and electronic shielding requirements. (separators and spectrometers; 1 part in 10^6)
- Continuous monitoring to detect short-term, non-linear fluctuations in the magnetic field. Efficient use of beam time -> Increase precision and sensitivity.

Measuring Magnetic Field with a Penning Trap

Uniform B-field



$$\omega_c = \frac{q}{m} B$$

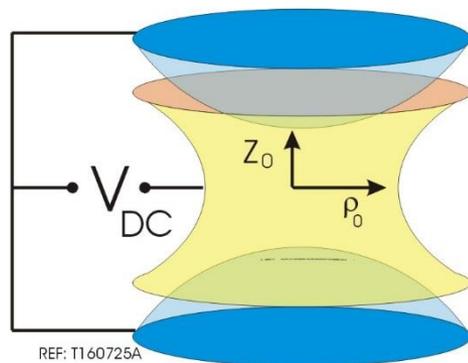
ω_c = cyclotron frequency

q = ion charge

m = ion mass

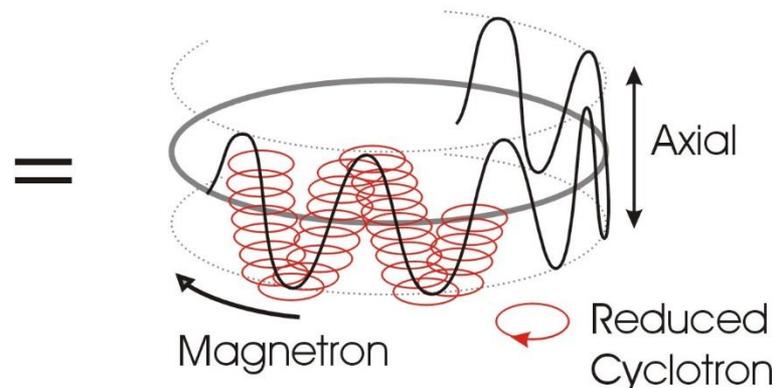
B = magnetic field

Quadrupole E-field



$$d = \sqrt{\frac{\rho_0^2}{4} + \frac{z_0^2}{2}}$$

3 Normal Modes



$$\omega_z = \sqrt{\frac{qV_{DC}}{md^2}}$$

$$\omega_{\pm} = \frac{\omega_c}{2} \pm \sqrt{\frac{\omega_c^2}{4} - \frac{\omega_z^2}{2}}$$

Normal frequency hierarchy

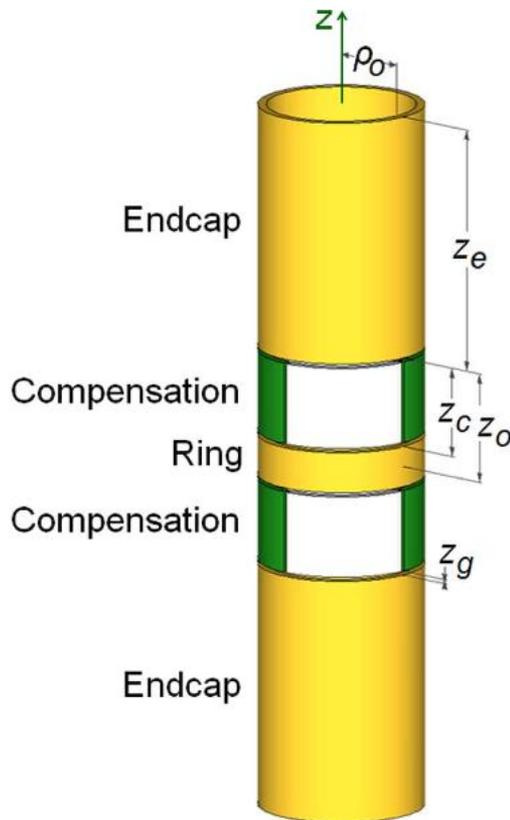
$$\omega_+ \gg \omega_z \gg \omega_-$$

detected in standard FT-ICR

$$\omega_c = \omega_+ + \omega_-$$

detected with quadrupole pickup FT-ICR

Cylindrical shaped, Open-endcap, Electrically compensated



Electrostatic potential only quadratic near trap center, more generally :

$$V = \frac{V_{DC}}{2} \sum_{n=0}^{\infty} C_n \left(\frac{r}{d}\right)^n P_n(\cos \theta)$$

$n = \text{odd}$ coefficients $C_n = 0$, symmetry

$n = 2$, C_2 represents quadrupole potential

$n = 4, 6, \dots$ anharmonic shifts to normal modes ω_z, ω_{\pm}

$$\frac{\Delta\omega_+}{\omega_+} = \frac{3}{2} \left(\frac{\omega_-}{\omega_+}\right)^2 C_4 \left(\frac{\rho_+}{d}\right)^2, \rho_+ \equiv \text{orbital radius}$$

$$\frac{\Delta\omega_+}{\omega_+} = -\frac{15}{8} \left(\frac{\omega_-}{\omega_+}\right)^2 C_6 \left(\frac{\rho_+}{d}\right)^4$$

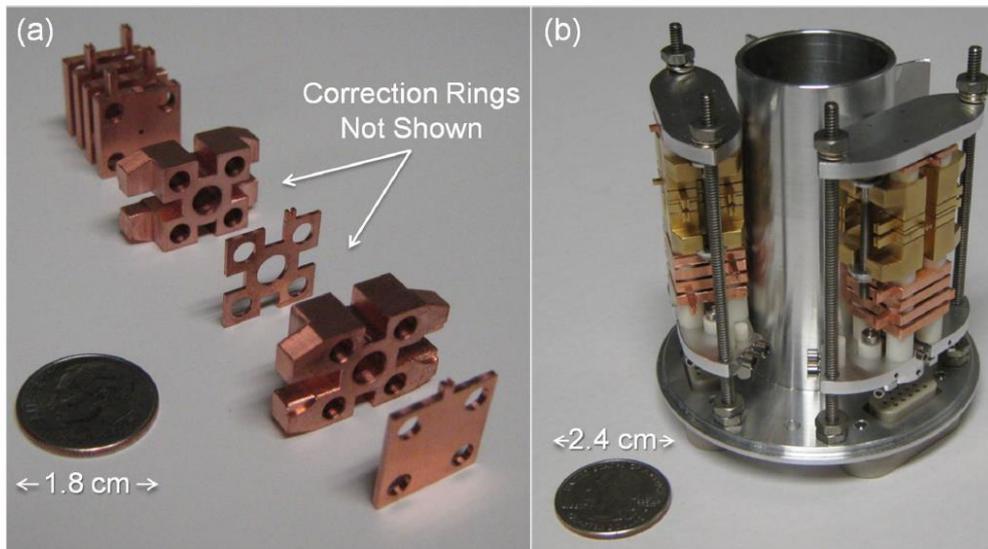
Minimize anharmonicity through proper dimensioning of electrodes.

Parameter	Value
ρ_o/z_o	0.990(13)
z_c/z_o	0.867(13)
z_e/z_o	2.970(14)
z_g/z_o	0.0495(40)
ρ_o	2.500(29) mm
z_o	2.525(29) mm
z_c	2.190(29) mm
z_e	7.500(26) mm
z_g	0.125(10) mm

Trap geometry "orthogonalized" via
G. Gabrielse et. al. 1989

$\frac{\rho_o}{z_o} \left(\frac{z_c}{z_o} \right)$ enable tuning $C_4 \rightarrow 0$ via V_c
without affecting ω_z & ω_{\pm}

$\frac{z_c}{z_o} \approx 0.835$, simultaneous tuning
 C_4 & $C_6 \rightarrow 0$

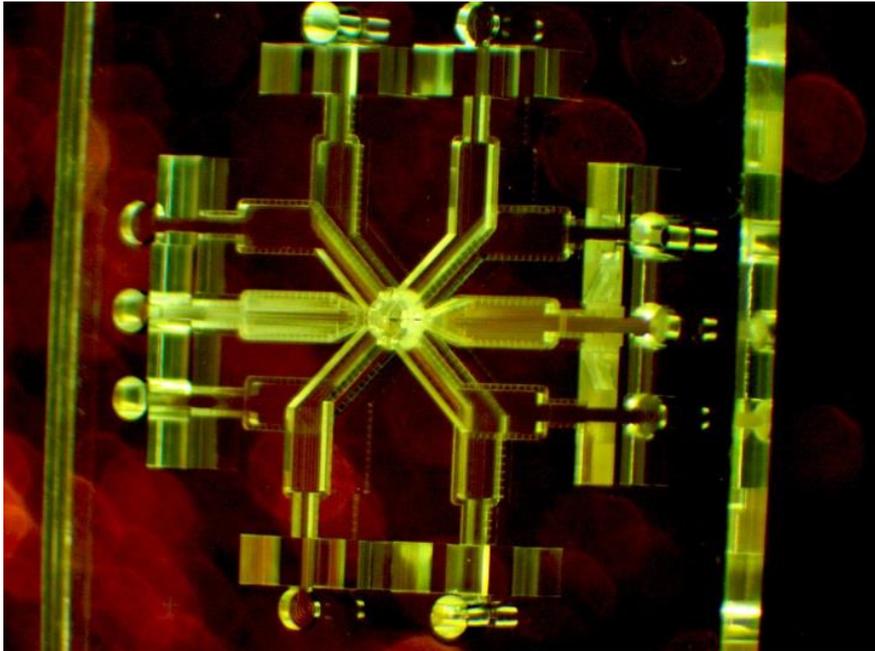


→ **Translume**

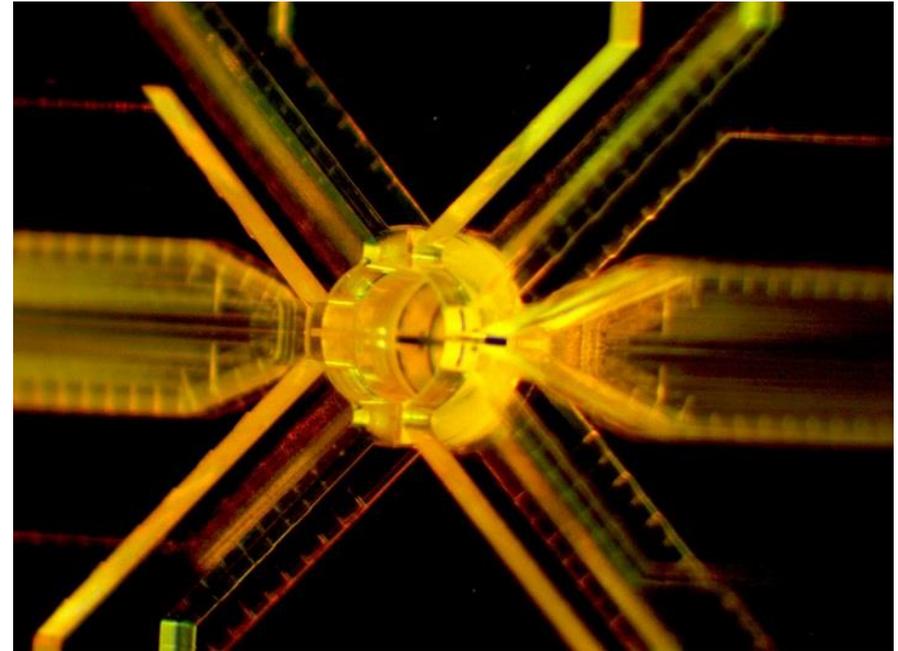


scale reduction and
component integration in
a fused silica platform

Ion Microtraps Fabricated Out of Fused Silica Glass : Step 1



Penning trap with 10 electrode access channels

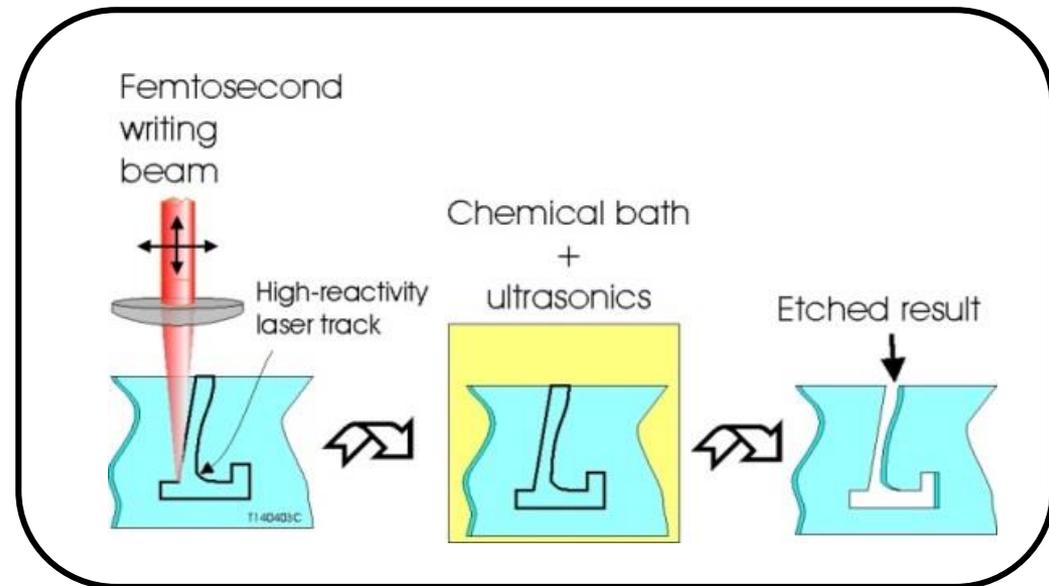
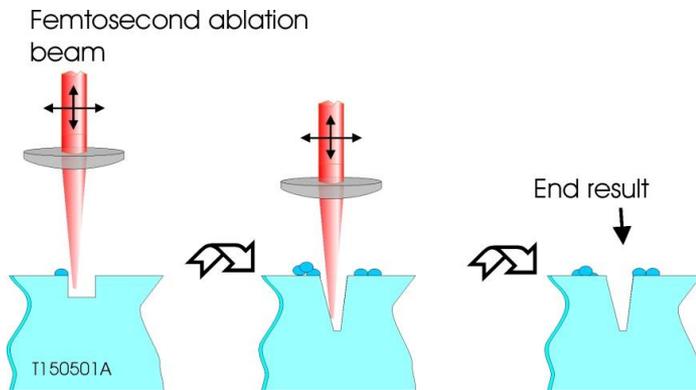


Penning trap central bore (1mm diameter)

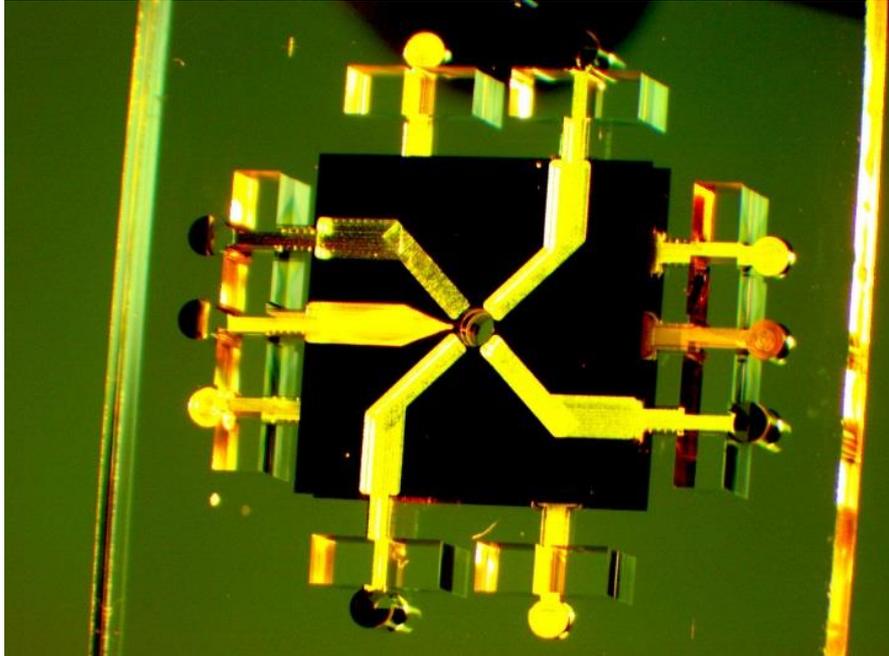
3D Laser patterning of the glass platform using *femtoEtch*TM process

Critical component formation and integration within a monolithic substrate

- NOT direct laser ablation of dielectrics
 - Debris generation, edge effects, *etc.*
- Combination of femtosecond laser direct-write and wet etching (*femtoEtch*) to shape fused silica
 - No ablation, no debris, no edge effects, true 3D geometry
 - Works best with fused silica glass



Ion Microtraps Fabricated Out of Fused Silica Glass : Step 2



Sputter coating: Au (1μ) on Ti (20nm)

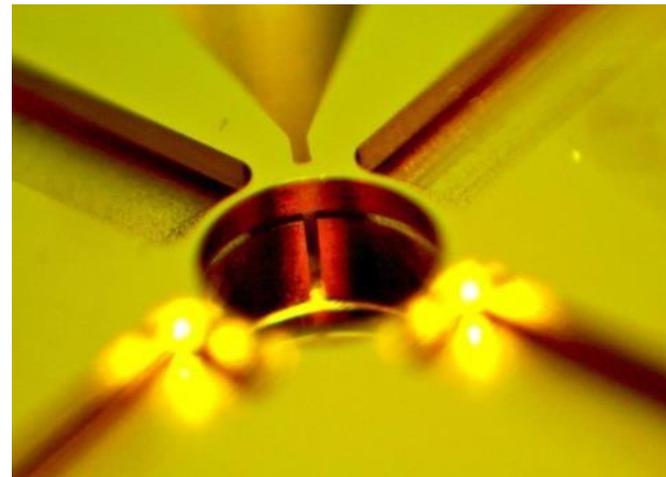
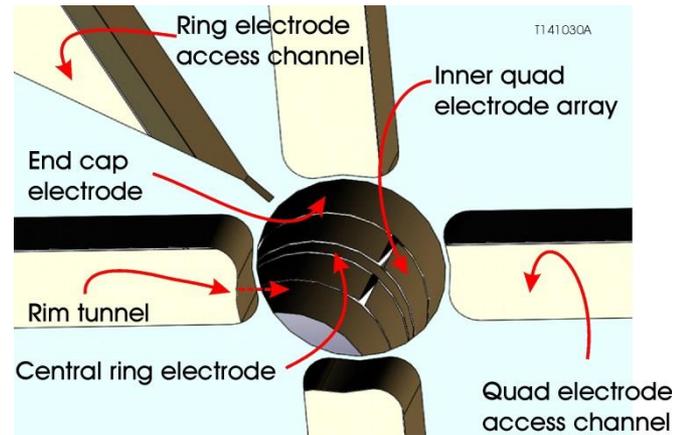
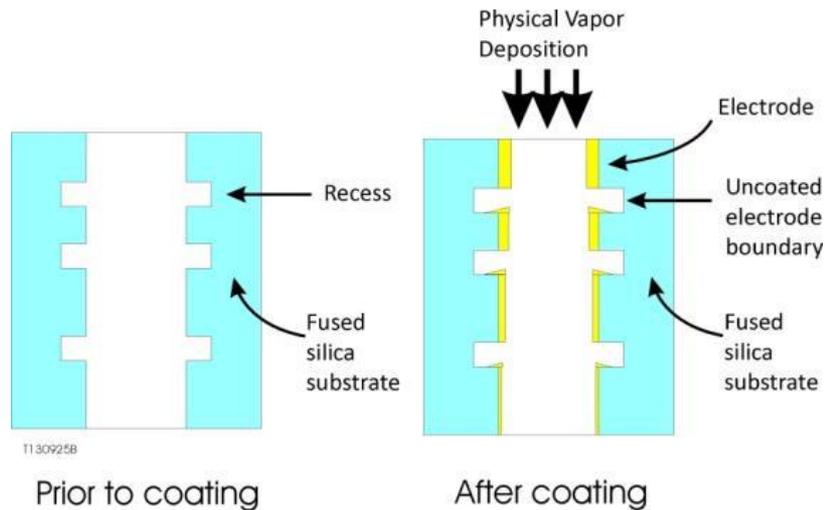


Coating from both sides for uniformity in center bore

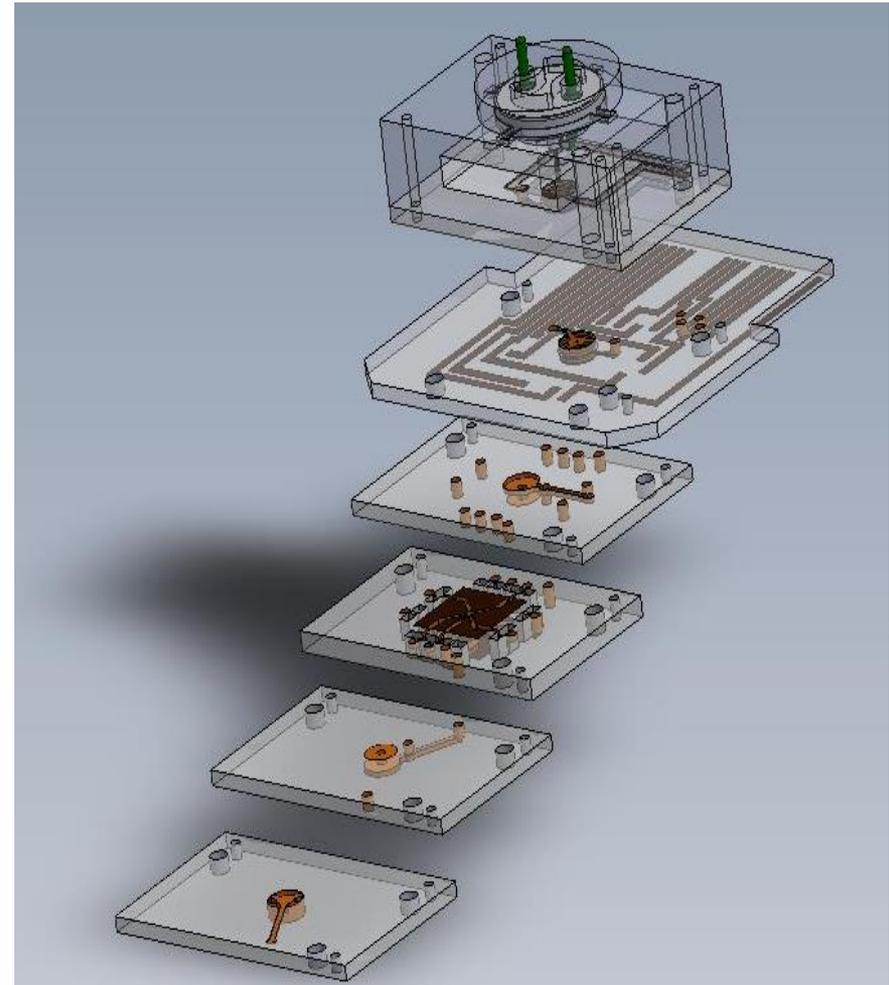
Metal coating of the 3D platform forming 3D electrodes

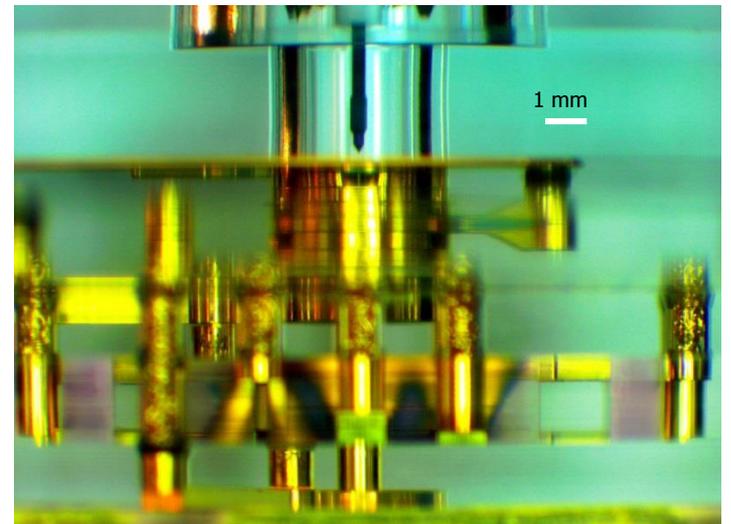
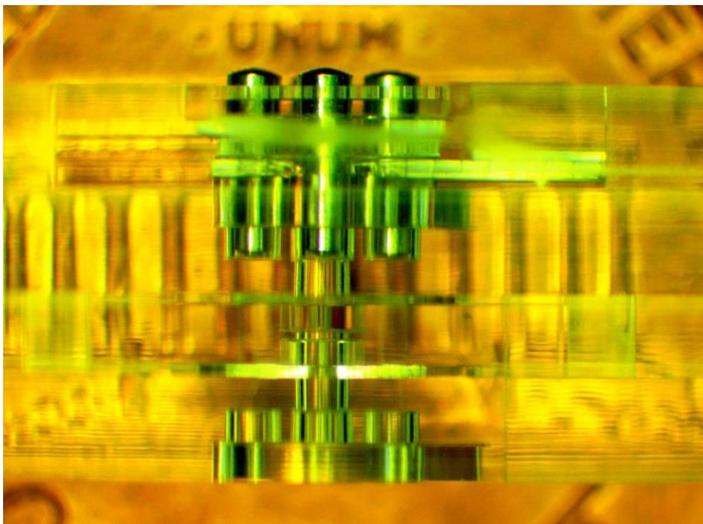
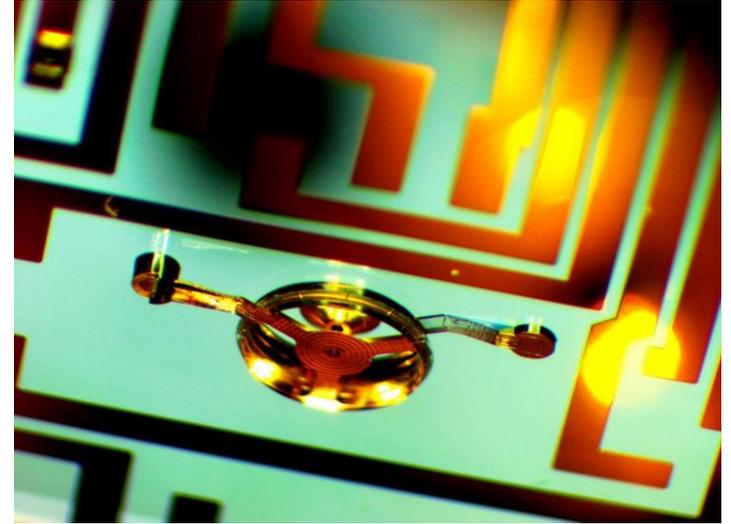
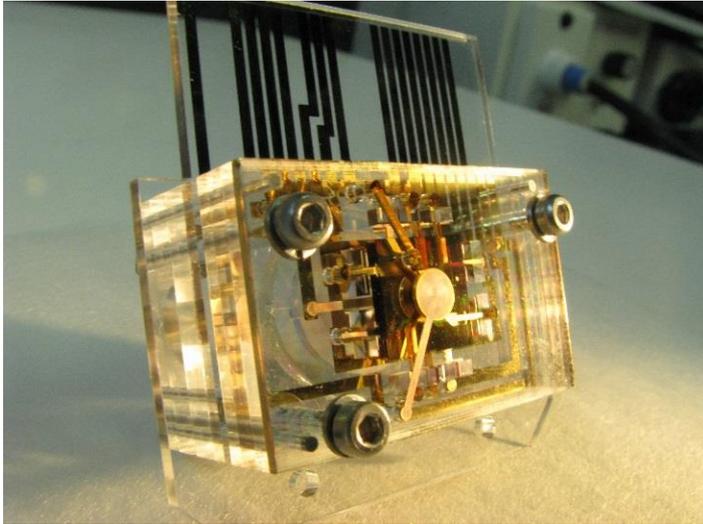
Creating 3D Electrodes Using in-substrate High-aspect Features

- Rely on the limited angular spread inherent in sputter coating to metalize contoured surfaces, including the side walls of recesses and high aspect features
- In some cases a secondary electro-plating process to increase coating thickness or extend coverage through tunnels
- Dielectric far from electrode interface



- For now ionization achieved with commercial thermal e^- emitter (LaB6)
- Trap electrode components fabricated monolithically within substrate
- Adjacent substrates aligned via precision hole & pin assemblies ($\pm 10\mu$)
- Electrical connection between substrates using “fuzz buttons”
- Electrode leads assembled on one surface for card connection and wiring
- All materials non-magnetic (Au on Ti coating, stainless steel, Au on BeCu)





- 1st generation device (5X reduced scale) is currently being tested in a 1.8T superconducting magnet at MSU
- 2nd device delivered with frame modifications for improved evacuation of trap bore and easier interconnect access
- 3rd device is currently being fabricated that is a 2.5X reduced scale of the original MSU minitrap
 - Compare with 1st generation device performance
- Reducing overall device size
 - Improve ionization source.
 - Redesign connector and cable assembly
- Sealed high vacuum probe

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